

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application of

Applicant : Powell, et al.  
Serial No. : 10/080,119  
Filed : February 21, 2002  
Title : METHOD OF FORMING A DIELECTRIC LAYER  
Docket : MIO 0060 VA (98-0814.01)  
Examiner : D. Le  
Art Unit : 2818

Assistant Commissioner for Patents  
Washington, DC 20231

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*Julie G. Cope*  
Attorney - Julie G. Cope

Reg. No. 48,624

Sir:

AMENDMENT

This paper is being filed in response to the office action mailed on October 8, 2002. Reconsideration is respectfully requested in light of the amendments and remarks below.

**CLEAN VERSION OF THE AMENDMENTS**

(A version of the amendments showing the markings is provided in a separate appendix attached to this paper.)

In the Specification

At page 1, line 1, the title should read:

--“METHOD OF FORMING A DIELECTRIC LAYER”--

At page 25, the Abstract should read:

“Methods for fabricating a dielectric layer are provided. In one embodiment, a silicon-containing material is deposited on a substrate. The deposited material is processed with a reactive agent to react with silicon atoms of the deposited material to form the dielectric layer. The silicon-containing dielectric layer can allow for improved